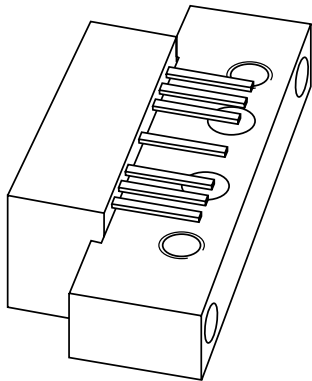


DATA SHEET



BGD802

860 MHz, 18.5 dB gain power
doubler amplifier

Product specification
Supersedes data of 2001 Oct 30

2002 Jan 23



860 MHz, 18.5 dB gain power doubler amplifier**BGD802****FEATURES**

- Excellent linearity
- Extremely low noise
- Excellent return loss properties
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

APPLICATIONS

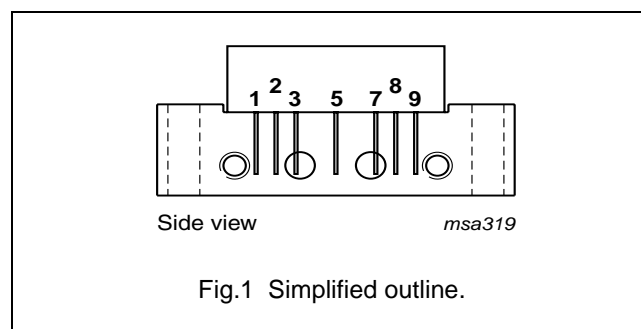
- CATV systems operating in the 40 to 860 MHz frequency range.

DESCRIPTION

Hybrid amplifier module in a SOT115J package operating at a supply voltage of 24 V (DC).

PINNING - SOT115J

| PIN | DESCRIPTION |
|------|-----------------|
| 1 | input |
| 2, 3 | common |
| 5 | +V _B |
| 7, 8 | common |
| 9 | output |

**QUICK REFERENCE DATA**

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|--------------------------------|-----------------------|------|------|------|
| G _p | power gain | f = 50 MHz | 18 | 19 | dB |
| | | f = 860 MHz | 18.5 | — | dB |
| I _{tot} | total current consumption (DC) | V _B = 24 V | — | 410 | mA |

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | MIN. | MAX. | UNIT |
|------------------|-------------------------------------|------|------|------|
| V _B | supply voltage | — | 25 | V |
| V _i | RF input voltage | — | 65 | dBmV |
| T _{stg} | storage temperature | −40 | +100 | °C |
| T _{mb} | operating mounting base temperature | −20 | +100 | °C |

860 MHz, 18.5 dB gain power doubler amplifier

BGD802

CHARACTERISTICS

Table 1 Bandwidth 40 to 860 MHz; $V_B = 24$ V; $T_{case} = 35$ °C; $Z_S = Z_L = 75$ Ω

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------|-----------------------------------|--|------|-----------|-----------|------|
| G_p | power gain | $f = 50$ MHz | 18 | 18.5 | 19 | dB |
| | | $f = 860$ MHz | 18.5 | 19.5 | – | dB |
| SL | slope cable equivalent | $f = 40$ to 860 MHz | 0.2 | 1.1 | 2 | dB |
| FL | flatness of frequency response | $f = 40$ to 860 MHz | – | ± 0.2 | ± 0.5 | dB |
| S_{11} | input return losses | $f = 40$ to 80 MHz | 20 | 35 | – | dB |
| | | $f = 80$ to 160 MHz | 18.5 | 31 | – | dB |
| | | $f = 160$ to 320 MHz | 17 | 27 | – | dB |
| | | $f = 320$ to 640 MHz | 15.5 | 22 | – | dB |
| | | $f = 640$ to 860 MHz | 14 | 20 | – | dB |
| S_{22} | output return losses | $f = 40$ to 80 MHz | 20 | 29.5 | – | dB |
| | | $f = 80$ to 160 MHz | 18.5 | 29 | – | dB |
| | | $f = 160$ to 320 MHz | 17 | 25.5 | – | dB |
| | | $f = 320$ to 640 MHz | 15.5 | 23 | – | dB |
| | | $f = 640$ to 860 MHz | 14 | 22 | – | dB |
| S_{21} | phase response | $f = 50$ MHz | –45 | – | +45 | deg |
| CTB | composite triple beat | 49 channels flat; $V_o = 47$ dBmV; measured at 859.25 MHz | – | –66 | –63 | dB |
| X_{mod} | cross modulation | 49 channels flat; $V_o = 47$ dBmV; measured at 55.25 MHz | – | –65 | –62 | dB |
| CSO | composite second order distortion | 49 channels flat; $V_o = 47$ dBmV; measured at 860.5 MHz | – | –67.5 | –60 | dB |
| d_2 | second order distortion | note 1 | – | –75 | –69 | dB |
| V_o | output voltage | $d_{im} = -60$ dB; note 2 | 61.5 | 63.5 | – | dBmV |
| NF | noise figure | $f = 50$ MHz | – | 4.5 | 5.5 | dB |
| | | $f = 550$ MHz | – | – | 6 | dB |
| | | $f = 650$ MHz | – | – | 7 | dB |
| | | $f = 750$ MHz | – | – | 7.5 | dB |
| | | $f = 860$ MHz | – | 6.5 | 9 | dB |
| I_{tot} | total current consumption (DC) | note 3 | – | 395 | 410 | mA |

Notes

- $f_p = 55.25$ MHz; $V_p = 44$ dBmV;
 $f_q = 805.25$ MHz; $V_q = 44$ dBmV;
measured at $f_p + f_q = 860.5$ MHz.
- Measured according to DIN45004B:
 $f_p = 851.25$ MHz; $V_p = V_o$;
 $f_q = 858.25$ MHz; $V_q = V_o - 6$ dB;
 $f_r = 860.25$ MHz; $V_r = V_o - 6$ dB;
measured at $f_p + f_q - f_r = 849.25$ MHz.
- The module normally operates at $V_B = 24$ V, but is able to withstand supply transients up to 30 V.

860 MHz, 18.5 dB gain power doubler amplifier

BGD802

Table 2 Bandwidth 40 to 860 MHz; $V_B = 24$ V; $T_{case} = 30$ °C; $Z_S = Z_L = 75 \Omega$

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------|-----------------------------------|--|------|-----------|-----------|------|
| G_p | power gain | $f = 50$ MHz | 18 | 18.5 | 19 | dB |
| | | $f = 860$ MHz | 18.5 | 19.5 | – | dB |
| SL | slope cable equivalent | $f = 40$ to 860 MHz | 0.2 | 1.1 | 2 | dB |
| FL | flatness of frequency response | $f = 40$ to 860 MHz | – | ± 0.2 | ± 0.5 | dB |
| S_{11} | input return losses | $f = 40$ to 80 MHz | 20 | 35 | – | dB |
| | | $f = 80$ to 160 MHz | 18.5 | 31 | – | dB |
| | | $f = 160$ to 320 MHz | 17 | 27 | – | dB |
| | | $f = 320$ to 640 MHz | 15.5 | 22 | – | dB |
| | | $f = 640$ to 860 MHz | 14 | 20 | – | dB |
| S_{22} | output return losses | $f = 40$ to 80 MHz | 20 | 29.5 | – | dB |
| | | $f = 80$ to 160 MHz | 18.5 | 29 | – | dB |
| | | $f = 160$ to 320 MHz | 17 | 25.5 | – | dB |
| | | $f = 320$ to 640 MHz | 15.5 | 23 | – | dB |
| | | $f = 640$ to 860 MHz | 14 | 22 | – | dB |
| S_{21} | phase response | $f = 50$ MHz | –45 | – | +45 | deg |
| CTB | composite triple beat | 129 channels flat; $V_o = 44$ dBmV; measured at 859.25 MHz | – | –56.5 | –54 | dB |
| X_{mod} | cross modulation | 129 channels flat; $V_o = 44$ dBmV; measured at 55.25 MHz | – | –61 | –59 | dB |
| CSO | composite second order distortion | 129 channels flat; $V_o = 44$ dBmV; measured at 860.5 MHz | – | –64.5 | –56 | dB |
| d_2 | second order distortion | note 1 | – | –75 | –69 | dB |
| V_o | output voltage | $d_{im} = -60$ dB; note 2 | 61.5 | 63 | – | dBmV |
| NF | noise figure | see Table 1 | – | – | – | dB |
| I_{tot} | total current consumption (DC) | note 3 | – | 395 | 410 | mA |

Notes

- $f_p = 55.25$ MHz; $V_p = 44$ dBmV;
 $f_q = 805.25$ MHz; $V_q = 44$ dBmV;
measured at $f_p + f_q = 860.5$ MHz.
- Measured according to DIN45004B:
 $f_p = 851.25$ MHz; $V_p = V_o$;
 $f_q = 858.25$ MHz; $V_q = V_o - 6$ dB;
 $f_r = 860.25$ MHz; $V_r = V_o - 6$ dB;
measured at $f_p + f_q - f_r = 849.25$ MHz.
- The module normally operates at $V_B = 24$ V, but is able to withstand supply transients up to 30 V.

860 MHz, 18.5 dB gain power doubler amplifier

BGD802

Table 3 Bandwidth 40 to 750 MHz; $V_B = 24$ V; $T_{case} = 30$ °C; $Z_S = Z_L = 75 \Omega$

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------|-----------------------------------|--|------|-------|-----------|------|
| G_p | power gain | $f = 50$ MHz | 18 | 18.5 | 19 | dB |
| | | $f = 750$ MHz | 18.5 | 19.4 | – | dB |
| SL | slope cable equivalent | $f = 40$ to 750 MHz | 0.2 | – | 2 | dB |
| FL | flatness of frequency response | $f = 40$ to 750 MHz | – | – | ± 0.5 | dB |
| s_{11} | input return losses | $f = 40$ to 80 MHz | 20 | 35 | – | dB |
| | | $f = 80$ to 160 MHz | 18.5 | 31 | – | dB |
| | | $f = 160$ to 320 MHz | 17 | 27 | – | dB |
| | | $f = 320$ to 640 MHz | 15.5 | 22 | – | dB |
| | | $f = 640$ to 750 MHz | 14 | 20 | – | dB |
| s_{22} | output return losses | $f = 40$ to 80 MHz | 20 | 29.5 | – | dB |
| | | $f = 80$ to 160 MHz | 18.5 | 29 | – | dB |
| | | $f = 160$ to 320 MHz | 17 | 25.5 | – | dB |
| | | $f = 320$ to 640 MHz | 15.5 | 23 | – | dB |
| | | $f = 640$ to 750 MHz | 14 | 22 | – | dB |
| s_{21} | phase response | $f = 50$ MHz | –45 | – | +45 | deg |
| CTB | composite triple beat | 110 channels flat; $V_o = 44$ dBmV; measured at 745.25 MHz | – | –60.5 | –58 | dB |
| X_{mod} | cross modulation | 110 channels flat; $V_o = 44$ dBmV; measured at 55.25 MHz | – | –62.5 | –60 | dB |
| CSO | composite second order distortion | 110 channels flat; $V_o = 44$ dBmV; measured at 746.5 MHz | – | –66 | –60 | dB |
| d_2 | second order distortion | note 1 | – | – | –72 | dB |
| V_o | output voltage | $d_{im} = -60$ dB; note 2 | 64 | – | – | dBmV |
| NF | noise figure | see Table 1 | – | – | – | dB |
| I_{tot} | total current consumption (DC) | note 3 | – | 395 | 410 | mA |

Notes

- $f_p = 55.25$ MHz; $V_p = 44$ dBmV;
 $f_q = 691.25$ MHz; $V_q = 44$ dBmV;
measured at $f_p + f_q = 746.5$ MHz.
- Measured according to DIN45004B:
 $f_p = 740.25$ MHz; $V_p = V_o$;
 $f_q = 747.25$ MHz; $V_q = V_o - 6$ dB;
 $f_r = 749.25$ MHz; $V_r = V_o - 6$ dB;
measured at $f_p + f_q - f_r = 738.25$ MHz.
- The module normally operates at $V_B = 24$ V, but is able to withstand supply transients up to 30 V.

860 MHz, 18.5 dB gain power doubler amplifier

BGD802

Table 4 Bandwidth 40 to 550 MHz; $V_B = 24$ V; $T_{case} = 30$ °C; $Z_S = Z_L = 75 \Omega$

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------|-----------------------------------|---|------|------|-----------|------|
| G_p | power gain | $f = 50$ MHz | 18 | 18.5 | 19 | dB |
| | | $f = 550$ MHz | 18.5 | 19.3 | – | dB |
| SL | slope cable equivalent | $f = 40$ to 550 MHz | 0.2 | – | 2 | dB |
| FL | flatness of frequency response | $f = 40$ to 550 MHz | – | – | ± 0.3 | dB |
| S_{11} | input return losses | $f = 40$ to 80 MHz | 20 | 35 | – | dB |
| | | $f = 80$ to 160 MHz | 18.5 | 31 | – | dB |
| | | $f = 160$ to 320 MHz | 17 | 27 | – | dB |
| | | $f = 320$ to 550 MHz | 16 | 22 | – | dB |
| S_{22} | input return losses | $f = 40$ to 80 MHz | 20 | 29.5 | – | dB |
| | | $f = 80$ to 160 MHz | 18.5 | 29 | – | dB |
| | | $f = 160$ to 320 MHz | 17 | 25.5 | – | dB |
| | | $f = 320$ to 550 MHz | 16 | 23 | – | dB |
| S_{21} | phase response | $f = 50$ MHz | –45 | – | +45 | deg |
| CTB | composite triple beat | 77 channels flat; $V_o = 44$ dBmV; measured at 547.25 MHz | – | –67 | –65 | dB |
| X_{mod} | cross modulation | 77 channels flat; $V_o = 44$ dBmV; measured at 55.25 MHz | – | –66 | –63 | dB |
| CSO | composite second order distortion | 77 channels flat; $V_o = 44$ dBmV; measured at 548.5 MHz | – | –67 | –63 | dB |
| d_2 | second order distortion | note 1 | – | – | –72 | dB |
| V_o | output voltage | $d_{im} = -60$ dB; note 2 | 65 | – | – | dBmV |
| NF | noise figure | see Table 1 | – | – | – | dB |
| I_{tot} | total current consumption (DC) | note 3 | – | 395 | 410 | mA |

Notes

- $f_p = 55.25$ MHz; $V_p = 44$ dBmV;
 $f_q = 493.25$ MHz; $V_q = 44$ dBmV;
measured at $f_p + f_q = 548.5$ MHz.
- Measured according to DIN45004B:
 $f_p = 540.25$ MHz; $V_p = V_o$;
 $f_q = 547.25$ MHz; $V_q = V_o - 6$ dB;
 $f_r = 549.25$ MHz; $V_r = V_o - 6$ dB;
measured at $f_p + f_q - f_r = 538.25$ MHz.
- The module normally operates at $V_B = 24$ V, but is able to withstand supply transients up to 30 V.

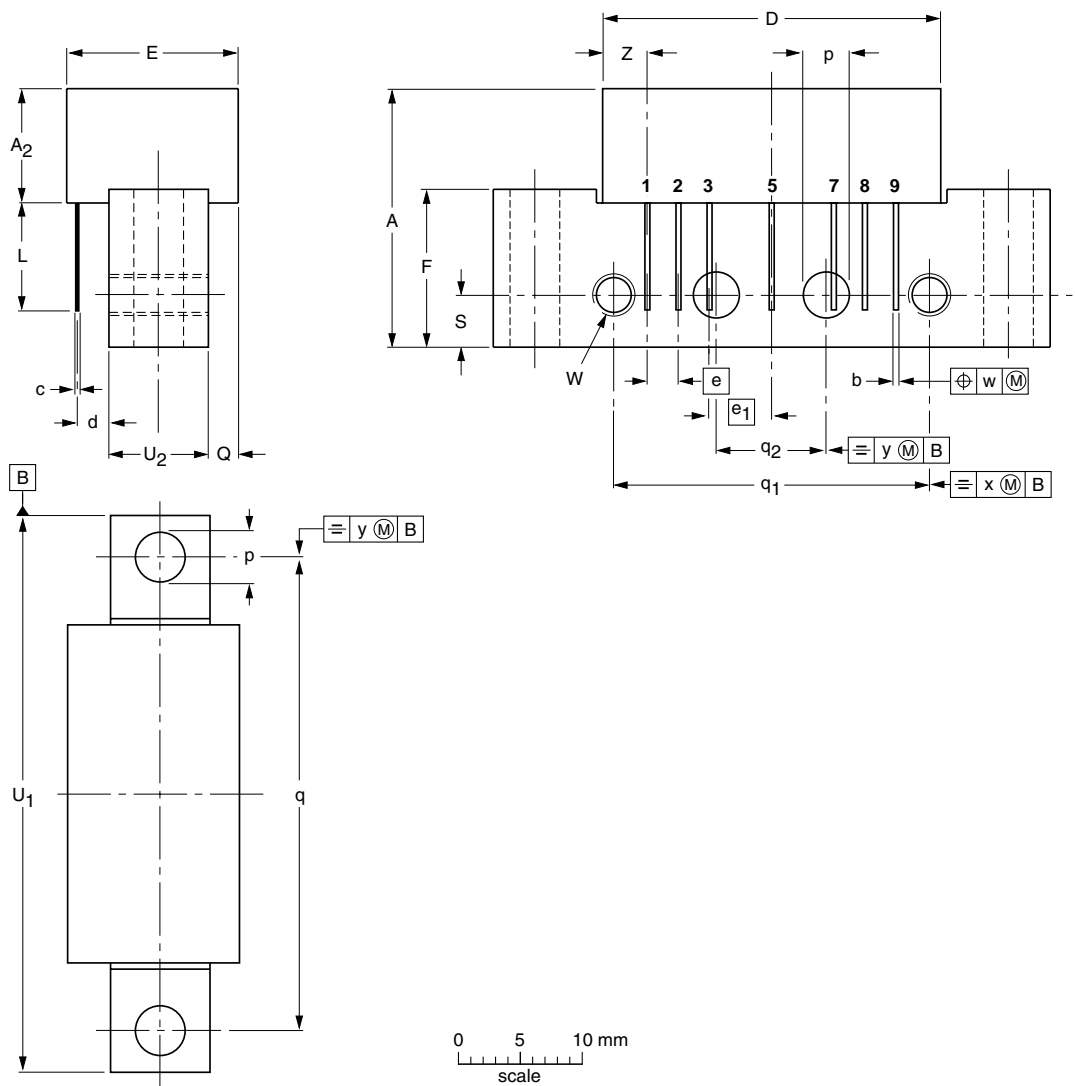
860 MHz, 18.5 dB gain power doubler amplifier

BGD802

PACKAGE OUTLINE


Rectangular single-ended package; aluminium flange; 2 vertical mounting holes;
2 x 6-32 UNC and 2 extra horizontal mounting holes; 7 gold-plated in-line leads

SOT115J



DIMENSIONS (mm are the original dimensions)

| UNIT | A max. | A ₂ max. | b | c | D max. | d | E max. | e | e ₁ | F | L min. | p | Q max. | q | q ₁ | q ₂ | S | U ₁ | U ₂ | W | w | x | y | Z max. |
|------|-----------|------------------------|--------------|------|-----------|--------------|-----------|------|----------------|------|-----------|--------------|-----------|------|----------------|----------------|-----|----------------|----------------|-------------|------|-----|-----|-----------|
| mm | 20.8 | 9.5 | 0.51 0.38 | 0.25 | 27.2 | 2.04 2.54 | 13.75 | 2.54 | 5.08 | 12.7 | 8.8 | 4.15 3.85 | 2.4 | 38.1 | 25.4 | 10.2 | 4.2 | 44.75 44.25 | 8.2 7.8 | 6-32 UNC | 0.25 | 0.7 | 0.1 | 3.8 |

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|--------------------|------------|-------|-------|--|---|----------------------|
| | IEC | JEDEC | JEITA | | | |
| SOT115J | | | | |  | 04-02-04 10-06-18 |

860 MHz, 18.5 dB gain power doubler amplifier

BGD802

DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|--------------------------------|-------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

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860 MHz, 18.5 dB gain power doubler amplifier

BGD802

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Contact information

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Printed in The Netherlands

613518/07/pp10

Date of release: 2002 Jan 23

Document order number: 9397 750 09191